EE3230 Introduction to Integrated Circuit Design, Fall 2021 Final Project

Due Date: 2022/01/18

Note

- 1. Do the simulation and analysis with cic018.1.
- 2. Power supply (VDD) = 1.8V.
- 3. Use .tran 1p XX for simulation

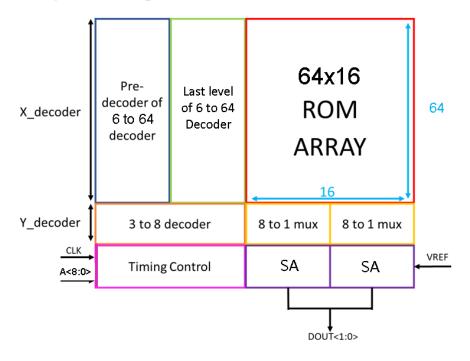
Design Part

- 1. Please design a 1024 bits ROM macro with access time < 5ns, described as follows: (40%)
 - A. 11-bit input: A<8:0>, CLK (100MHz, rise/fall time = 0.01ns), VREF.
 - B. 2-bit output: DOUT<1:0> (Output loading is neglected)
 - C. Pre-sim: TT25°C, SS25°C, FF25°C, SF25°C, FS25°C
 - D. Post-sim: TT25°C
- 2. Print out your schematic and simulation waveforms with **5 corners**. Waveforms should show at least 2 cycles including read 0 and read 1, measure the average power and access time. (10%)
- 3. Complete the layout of your ROM macro and measure its area. (30%)
- 4. Run post-sim (with R-C-CC extraction) at TT 25°C, compare the result and waveform with pre-sim. (10%)
- 5. Fill in the google sheet with your post-simulation at TT 25°C for ranking.

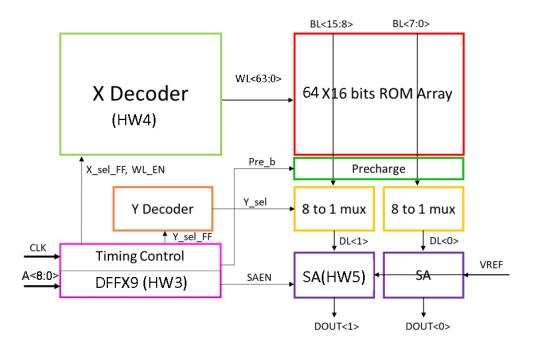
 (FOM = access time² * power * area)

 *(access time^2*power) in FOM is also known as EDP(energy-delay product)
- 6. Describe how you design each block of the ROM macro. (10%)

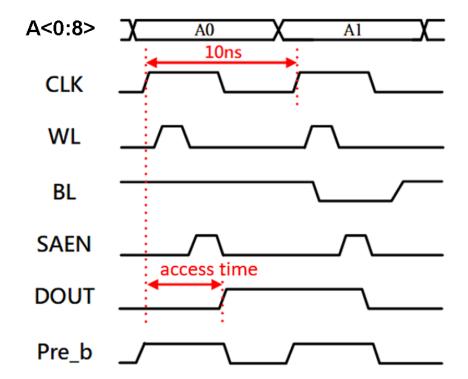
Block Diagram Example



Detail Block Diagram

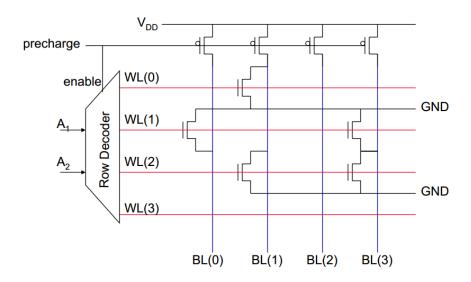


Example Waveform

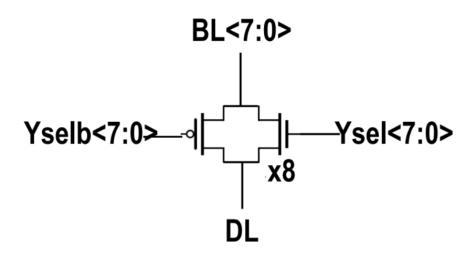


Attached Information

- 1. ROM array (NOR Type ROM):
- *ROM gds is attached in HW3. You should construct the schematic of ROM array by yourself.



2. YMUX_8_to_1: Select one of eight BLs and send it to the sense amplifier.



- 3. DFF: HW3
- 4. X decoder: HW4
- 5. Sense amplifier: HW5
- 6. Timing Control: Use combinational logics to generate timing control signals SAEN, Pre_b, and WL_EN.

^{*}You can redesign any circuit to get a better FOM except ROM array.

Bonus (access time² * power * area)

1 st (10%)

2 nd ~ 10th (8%)

11th ~ 20th (5%)

21 th \sim 40 th (3%)

Note: The less, the better.

Submission

- 1. IEEE format report (Final_TeamXX.pdf)
- 2. Hspice files (.sp/.spi)
- 3. Gds file (.gds)